

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HSB2838

Silicon Epitaxial Planar Diode for High Speed Switching



ADE-208-486A (Z)

Rev.1
Mar. 2002

Features

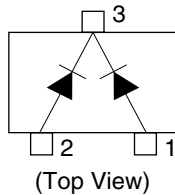
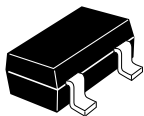
- Fast recovery time.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSB2838	A6	CMPAK

www.DataSheet4U.com

Pin Arrangement



1. Anode
2. Anode
3. Cathode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Average rectified current	I_O^{*1}	100	mA
Peak forward current	I_{FM}^{*1}	300	mA
Non-Repetitive peak forward surge current	I_{FSM}^{*2}	4	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−55 to +125	°C

Notes: 1. Two device total.
2. Value at duration of 1 μsec, two device total.

Electrical Characteristics *

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	—	—	1.0	V	$I_F = 10\text{ mA}$
	V_{F2}	—	—	1.0		$I_F = 50\text{ mA}$
	V_{F3}	—	—	1.2		$I_F = 100\text{ mA}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 80\text{ V}$
Capacitance	C	—	—	2.0	pF	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$
Reverse recovery time	t_{rr}	—	—	3.0	ns	$I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 50\text{ }\Omega$

Note: Per one device.

Main Characteristic

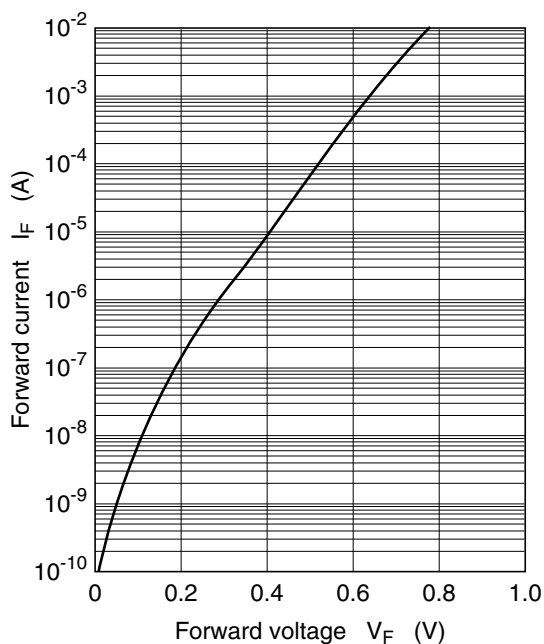


Fig.1 Forward current vs. Forward voltage

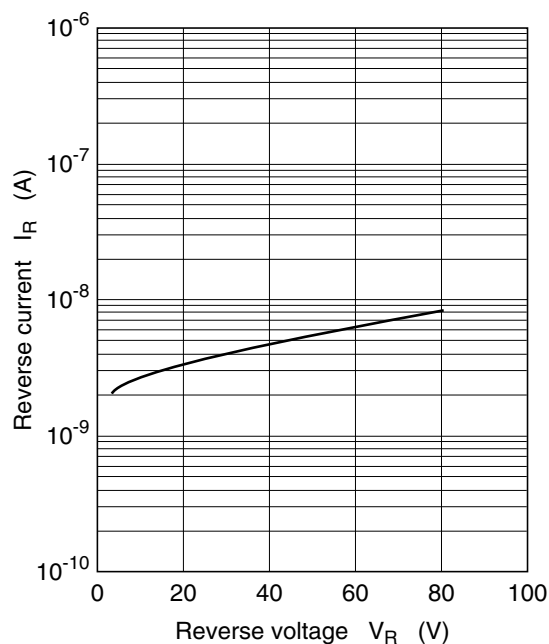


Fig.2 Reverse current vs. Reverse voltage

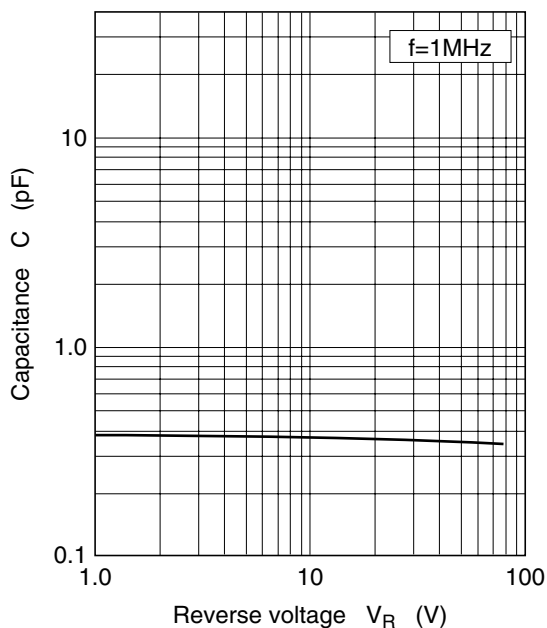


Fig.3 Capacitance vs. Reverse voltage

